

ABSTRACT OF THE DISCLOSURE

A method of forming junction isolation to isolate active elements. A substrate having a plurality of active areas and an isolation area between active areas is provided. A first gate structure is formed on part of the substrate located in the active areas and, simultaneously, a second gate structure serving as a dummy gate structure is formed on the substrate located in the isolation area. A first doped region is formed in the substrate located at two sides of the first and the second gate structures. A bottom anti-reflection layer is formed on the substrate, the first gate structure and the second gate structure. Part of the bottom anti-reflection layer is etched to expose the second gate structure. The second gate structure is removed to expose the substrate. A second doped region serving as a junction isolation region is formed in the substrate located in the isolation area.